

## NCE N-Channel Super Trench II Power MOSFET

### Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

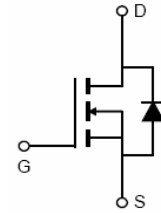
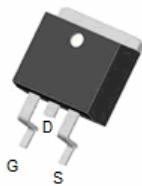
- $V_{DS} = 120V, I_D = 70A$   
 $R_{DS(ON)} = 8.5m\Omega$ , typical (TO-220) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 8.2m\Omega$ , typical (TO-263) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

**100% UIS TESTED!**  
**100%  $\Delta V_{ds}$  TESTED!**

TO-220



TO-263



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP10N12	NCEP10N12	TO-220	-	-	-
NCEP10N12D	NCEP10N12D	TO-263	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	120	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	70	A
Drain Current-Continuous ( $T_C = 100^\circ C$ )	$I_D (100^\circ C)$	50	A
Pulsed Drain Current	$I_{DM}$	280	A
Maximum Power Dissipation	$P_D$	120	W
Derating factor		0.8	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 4)</sup>	$E_{AS}$	352	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	$^\circ C/W$
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## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
<b>Off Characteristics</b>							
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	120		-	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=120V, V_{GS}=0V$	-	-	1	$\mu A$	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA	
<b>On Characteristics</b> (Note 3)							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=35A$	TO-220	-	8.5	10.0	m $\Omega$
			TO-263		8.2	10.0	
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=35A$		60	-	S	
<b>Dynamic Characteristics</b> (Note 3)							
Input Capacitance	$C_{iss}$	$V_{DS}=60V, V_{GS}=0V,$ $F=1.0MHz$	-	3050	-	pF	
Output Capacitance	$C_{oss}$		-	280	-	pF	
Reverse Transfer Capacitance	$C_{rss}$		-	22	-	pF	
<b>Switching Characteristics</b> (Note 3)							
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=60V, I_D=35A$ $V_{GS}=10V, R_G=1.6\Omega$	-	15	-	nS	
Turn-on Rise Time	$t_r$		-	10	-	nS	
Turn-Off Delay Time	$t_{d(off)}$		-	34	-	nS	
Turn-Off Fall Time	$t_f$		-	8	-	nS	
Total Gate Charge	$Q_g$	$V_{DS}=60V, I_D=35A,$ $V_{GS}=10V$	-	53	-	nC	
Gate-Source Charge	$Q_{gs}$		-	20	-	nC	
Gate-Drain Charge	$Q_{gd}$		-	12.5	-	nC	
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage (Note 2)	$V_{SD}$	$V_{GS}=0V, I_S=35A$	-	-	1.2	V	
Diode Forward Current	$I_S$		-	-	70	A	
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}, I_F = 35A$ $di/dt = 100A/\mu s$ (Note 3)	-	60	-	nS	
Reverse Recovery Charge	$Q_{rr}$		-	106	-	nC	

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
3. Guaranteed by design, not subject to production
4. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.25mH, R_g=25\Omega$

Typical Electrical and Thermal Characteristics

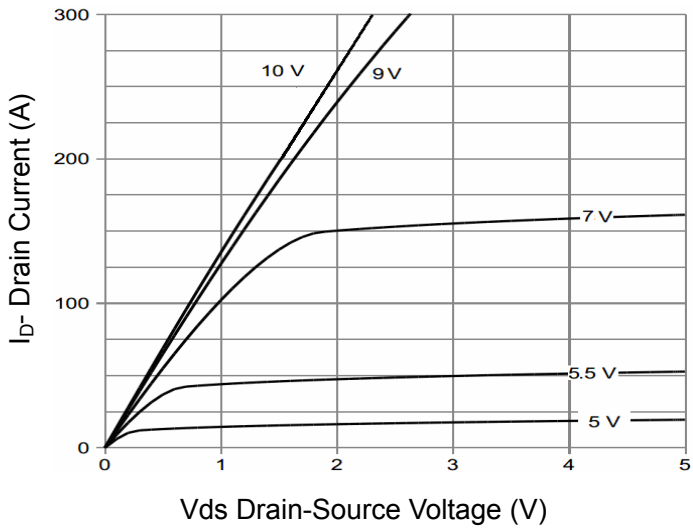


Figure 1 Output Characteristics

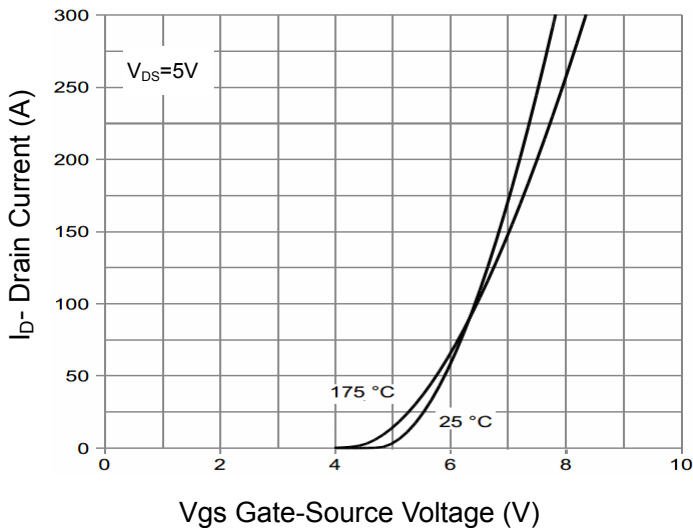


Figure 2 Transfer Characteristics

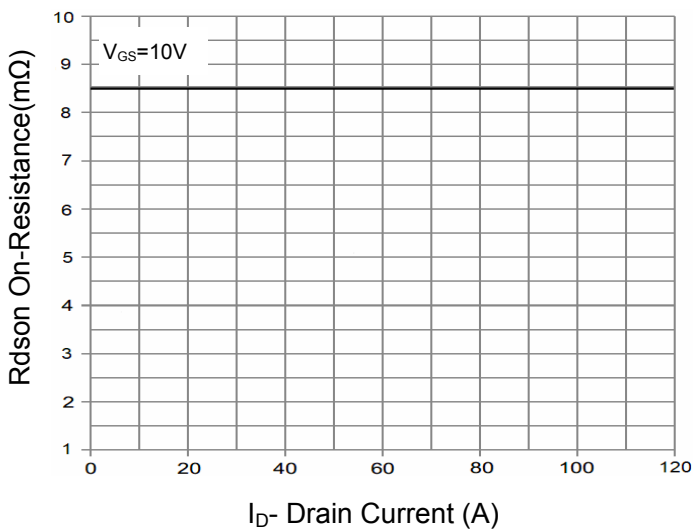


Figure 3 Rdson- Drain Current

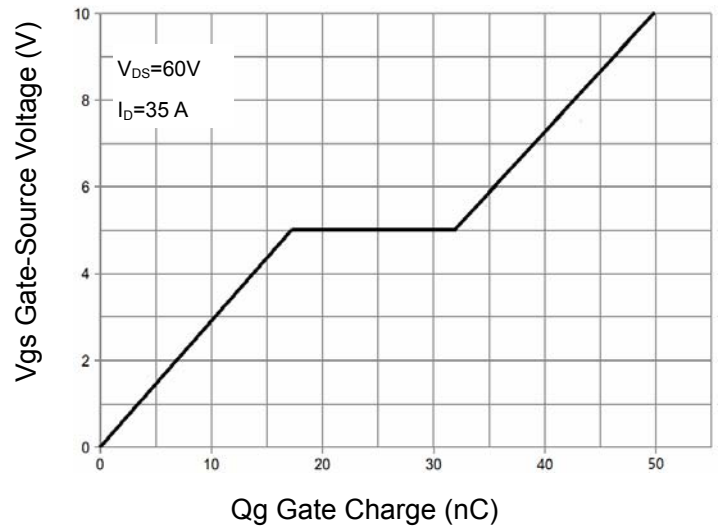


Figure 4 Gate Charge

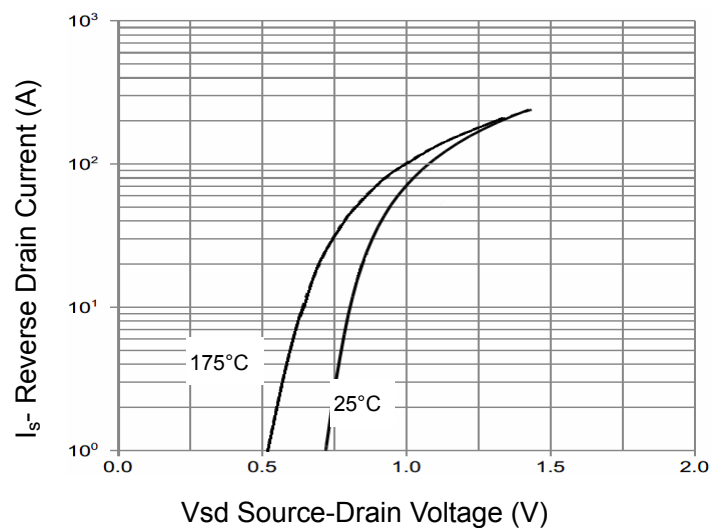


Figure 5 Source- Drain Diode Forward

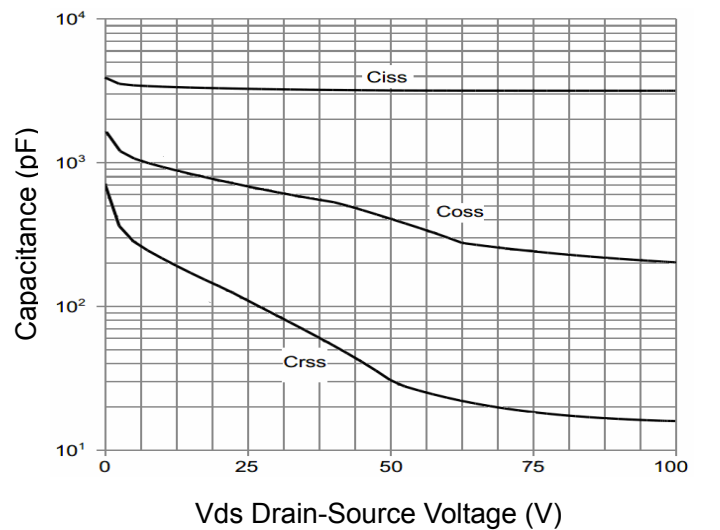
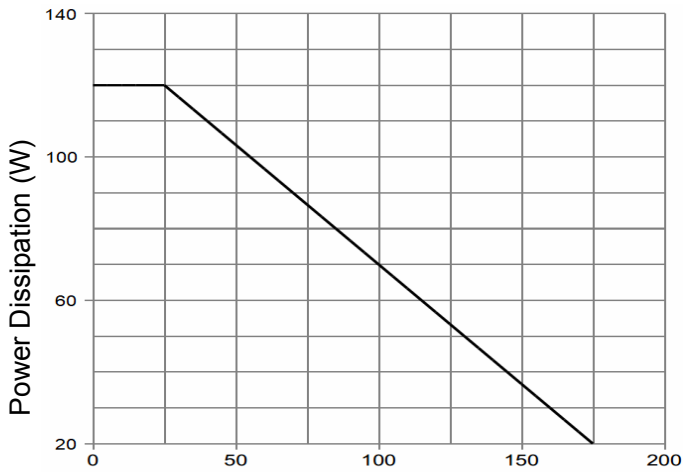
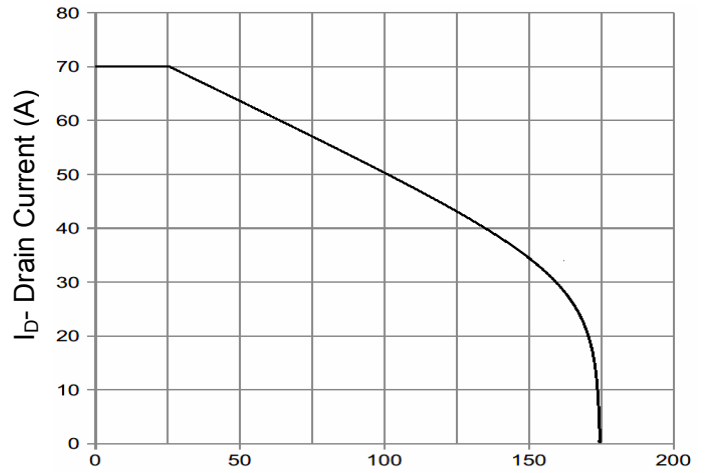


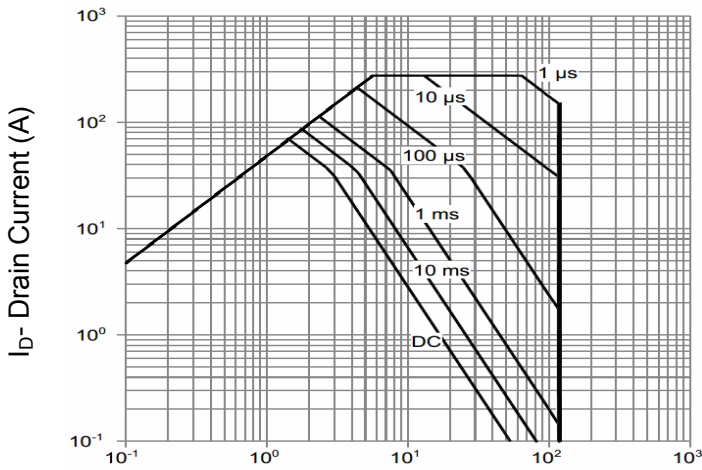
Figure 6 Capacitance vs Vds



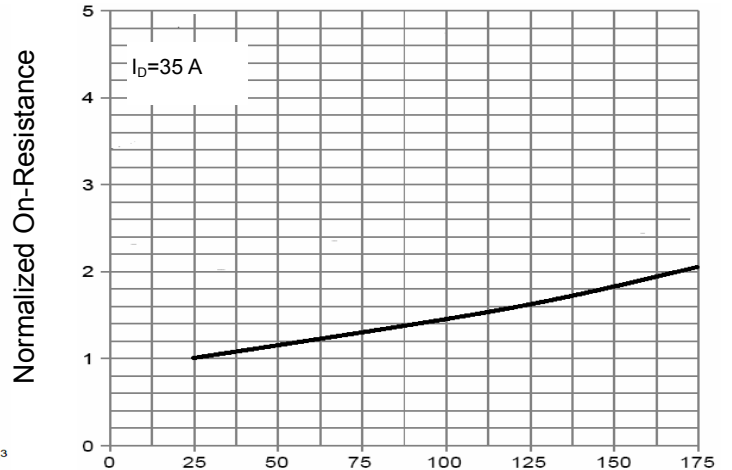
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 7 Power De-rating**



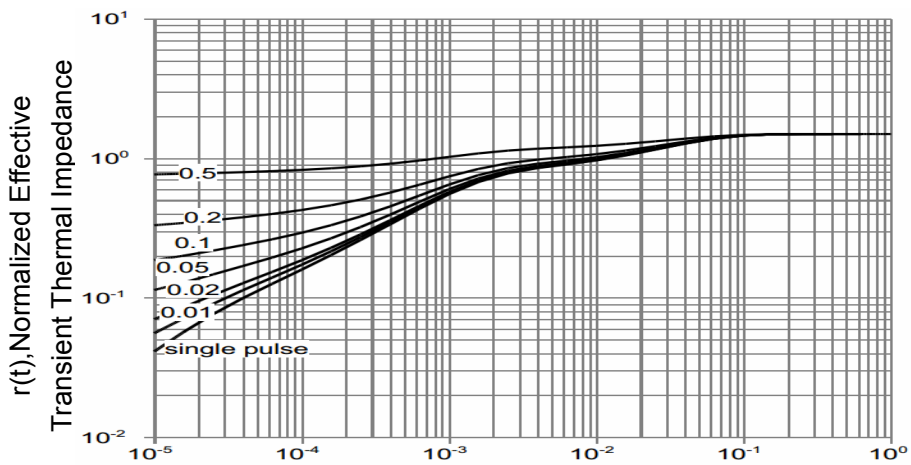
T<sub>J</sub>-Junction Temperature (°C)  
**Figure 9 Current De-rating**



V<sub>ds</sub> Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**



T<sub>J</sub>-Junction Temperature(°C)  
**Figure 10 Rdson-Junction Temperature**



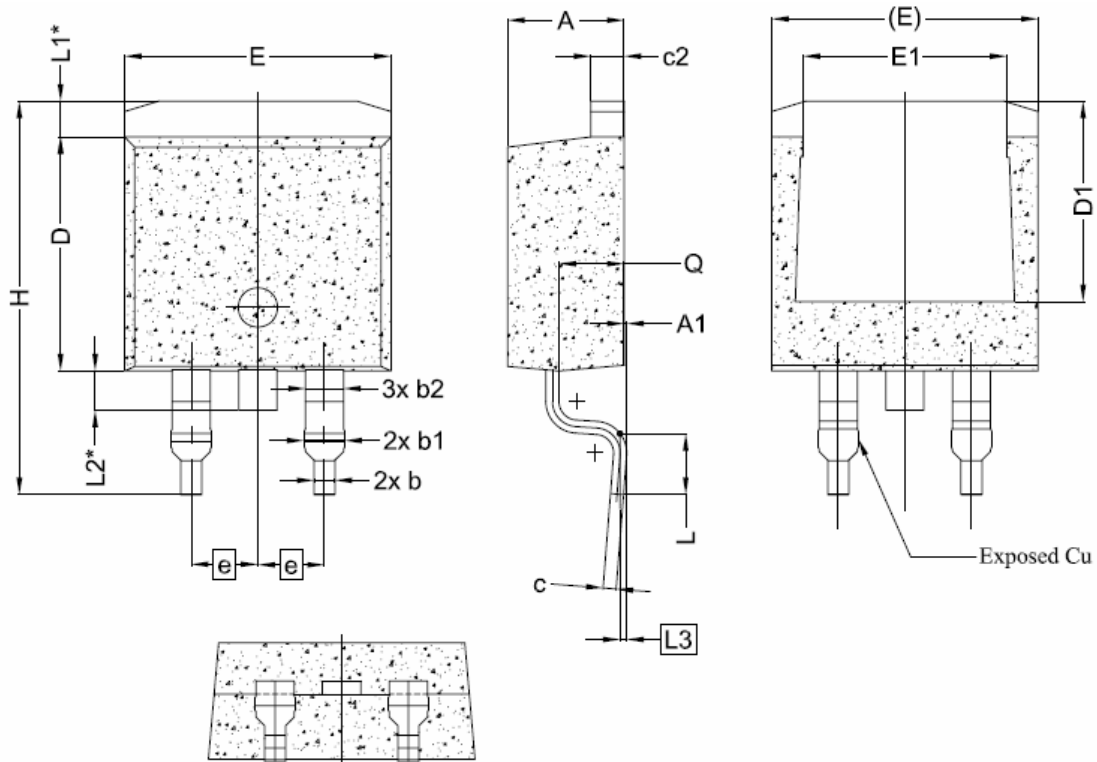
Square Wave Pluse Duration(sec)  
**Figure 11 Normalized Maximum Transient Thermal Impedance**

## TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	-
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

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